TOSHIBA

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HCT573AP,TC74HCT573AF

Octal D-Type Latch with 3-State Output

The TC74HCT573A is a high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Its inputs are compatible with TTL, NMOS, and CMOS output voltage levels.

Its 8-bit D-type latch is controlled by a latch enable input (LE) and an output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

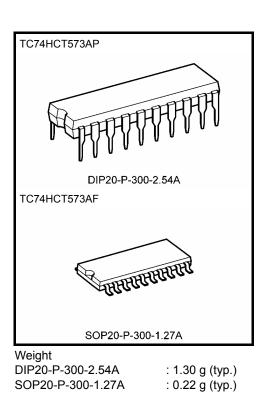
Features

- High speed: $t_{pd} = 18 \text{ ns}$ (typ.) at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max)}$ at $Ta = 25^{\circ}C$
- Compatible with TTL outputs: V_{IL} = 0.8 V (max)
 - $V_{IH} = 2.0 V (min)$
- Output drive capability: 15 LSTTL loads
- Symmetrical output impedance: $|I_{OH}| = I_{OL} = 6 \text{ mA} (\text{min})$
- $\bullet \quad \text{Balanced propagation delays: } t_{pLH} \simeq t_{pHL}$
- Pin and function compatible with $74\mathrm{LS}573$

Pin Assignment

ŌE	1		20	V _{cc}
D0	2	1	19	Q0
D1	2 3	1	18	Q1
D2		1	17	Q2
D3	5	1	16	Q3
D4	6	1	15	Q4
D5	7	1	14	Q5
D6	8	1	13	Q6
D7	9	1	12	Q7
GND	10	1	1 11	LE

(TOP VIEW)



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IEC Logic Symbol

<u>OE</u> <u>(1)</u> LE <u>(11)</u>	EN C1	
$\begin{array}{c} D0 & (2) \\ (3) \\ D1 & (4) \\ D2 & (5) \\ D3 & (6) \\ D4 & (7) \\ D5 & (8) \\ D6 & (9) \\ D7 & \end{array}$	1D	(19) (18) Q1 (17) Q2 (16) Q3 (15) Q4 (14) Q5 (13) Q6 (12) Q7

Truth Table

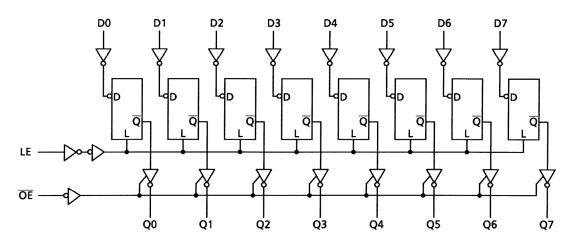
	Inputs					
ŌĒ	LE	D	Q			
Н	Х	Х	Z			
L	L	Х	Qn			
L	Н	L	L			
L	Н	Н	Н			

X: Don't care

Z: High impedance

 $\mathsf{Q}_{\mathsf{n}}:\mathsf{Q}$ outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7	V
DC input voltage	VIN	-0.5~V _{CC} + 0.5	V
DC output voltage	Vout	-0.5~V _{CC} + 0.5	V
Input diode current	lік	±20	mA
Output diode current	I _{OK}	±20	mA
DC output current	IOUT	±35	mA
DC V _{CC} /ground current	I _{CC}	±75	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C shall be applied until 300 mW.

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5~5.5	V
Input voltage	VIN	0~V _{CC}	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	t _r , t _f	0~500	ns

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics	Symbol		Test Condition		Ta = 25°C			Ta = -40~85°C		Unit
Ondradichotico Oymbol				$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Onit
High-level input voltage	VIH	—		4.5~5.5	2.0	_	_	2.0	_	V
Low-level input voltage	VIL	—		4.5~5.5	_	_	0.8	_	0.8	V
High-level output	V _{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -20 \ \mu A$	4.5	4.4	4.5		4.4	_	V
voltage	litage VOH		$I_{OH} = -6 \text{ mA}$	4.5	4.18	4.31		4.13		v
Low-level output	V _{OL}	VIN	$I_{OL} = 20 \ \mu A$	4.5		0.0	0.1		0.1	V
voltage	۷OL	$= V_{IH} \text{ or } V_{IL}$	$I_{OL} = 6 \text{ mA}$	4.5		0.17	0.26		0.33	v
3-state output off-state current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or } GND$		5.5		_	±0.5	_	±5.0	μA
Input leakage current	I _{IN}	$V_{IN} = V_{CC}$ or GND		5.5	_	_	±0.1	_	±1.0	μA
	Icc	$V_{IN} = V_{CC}$ or	$V_{IN} = V_{CC}$ or GND			_	4.0		40.0	μA
Quiescent supply current	Ι _C	Per input: $V_{\rm IN} = 0.5 V \text{ or } 2.4 V$		5.5	_	_	2.0	_	2.9	mA

Timing Requirements (input: tr = tf = 6 ns)

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = _40 ~85°C	Unit
			V _{CC} (V)	Тур.	Limit	Limit	
Minimum pulse width	*		4.5	_	15	19	20
(LE)	^t W (H)		5.5	—	14	17	ns
Minimum set-up time	+		4.5		10	13	20
(data)	ts		5.5	—	9	11	ns
Minimum hold time	+ .		4.5	_	5	5	20
(data)	t _h		5.5	—	5	5	ns

AC Characteristics (input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -4	Га = -40~85°С		
Characteristics	Symbol		CL (pF)	$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Unit
Output transition time	t _{TLH}		50	4.5	_	7	12	_	15	ns
	t _{THL}		50	5.5		6	11	—	14	115
			50	4.5		19	29	—	36	
Propagation delay time	t _{pLH}		50	5.5	_	17	26		33	ns
(LE-Q)	t _{pHL}		150	4.5	_	24	37	—	46	115
			150	5.5	_	22	34		43	
			50	4.5	_	17	26	—	33	
Propagation delay time	t _{pLH}		50	5.5	_	14	23		29	ns
(D-Q)	t _{pHL}		150	4.5	_	22	34	—	43	110
			150	5.5		20	31	—	39	
	t _{pZL}	t_{pZL} $R_L = 1 k\Omega$	50	4.5	_	18	27	—	34	
Output enable time			50	5.5	_	15	24		30	ns
Output chable time	^t pZH		150	4.5	_	23	35	—	44	115
			150	5.5		20	32	—	40	
Output disable time	t _{pLZ}	$R_L = 1 k\Omega$	50	4.5	_	18	24	—	30	ns
	t _{pHZ}	TVL - T K52	50	5.5		16	22	—	28	115
Input capacitance	CIN	_	-		—	5	10		10	pF
Output capacitance	C _{OUT}		_		_	10	_	_	_	pF
Power dissipation capacitance	C _{PD} (Note)	_	_			38	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

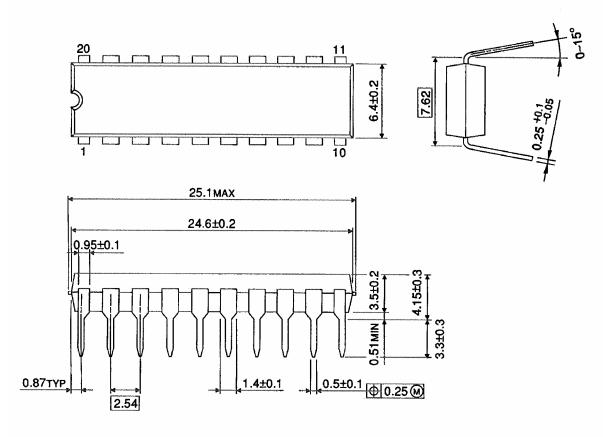
And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

C_{PD} (total) = 25 + 13 ⋅ n

Package Dimensions

DIP20-P-300-2.54A

Unit : mm



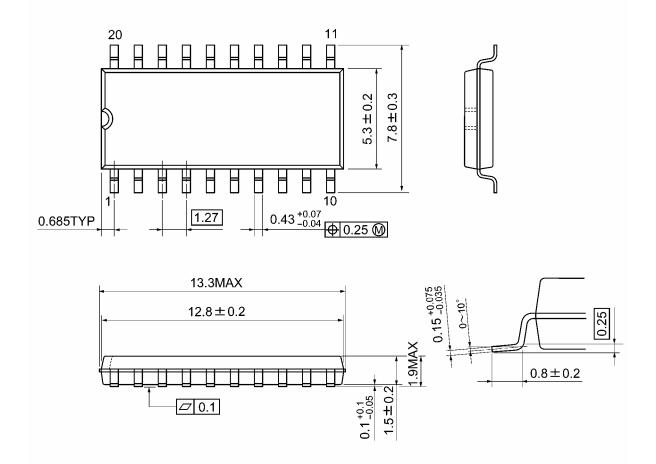
Weight: 1.30 g (typ.)

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Package Dimensions

SOP20-P-300-1.27A

Unit: mm



Weight: 0.22 g (typ.)

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20070701-EN GENERAL

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